## **ABSTRACT**

Method and structure for integrating conductive and dielectric materials in a microelectronic structure having air gaps are disclosed. Certain embodiments of the invention comprise isolating dielectric layers from conductive layers using an etch stop layer to facilitate controlled removal of portions of the dielectric layers and formation of air gaps or voids. Capping and peripheral structural layers may be incorporated to increase the structural integrity of the integration subsequent to removal of sacrificial material.